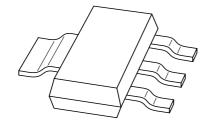
DISCRETE SEMICONDUCTORS

DATA SHEET



BAT120 seriesSchottky barrier double diodes

Product data sheet Supersedes data of 2001 Aug 27 2003 Aug 04



Schottky barrier double diodes

BAT120 series

FEATURES

- · Low switching losses
- · Capability of absorbing very high surge current
- Fast recovery time
- · Guard ring protected
- Plastic SMD package.

APPLICATIONS

- Low power switched-mode power supplies
- Rectification
- · Polarity protection.

DESCRIPTION

Planar Schottky barrier double diodes encapsulated in a SOT223 plastic SMD package.

MARKING

TYPE NUMBER	MARKING CODE
BAT120A	AT120A
BAT120C	AT120C
BAT120S	AT120S

PINNING

PIN	BAT120						
PIN	Α	С	S				
1	k ₁	a ₁	a ₁				
2	n.c.	n.c.	n.c.				
3	k ₂	a_2	k ₂				
4	a ₁ , a ₂	k ₁ , k ₂	k ₁ , a ₂				

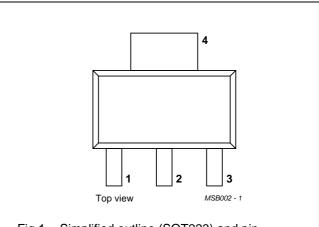
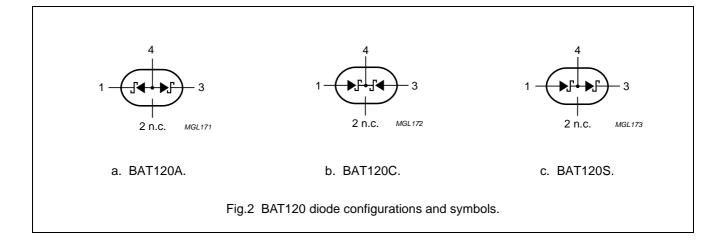


Fig.1 Simplified outline (SOT223) and pin configuration.



Schottky barrier double diodes

BAT120 series

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode					
V _R	continuous reverse voltage		_	25	V
I _F	continuous forward current		_	1	Α
I _{FSM}	non-repetitive peak forward current	t _p < 10 ms; half sinewave; JEDEC method	_	10	А
I _{RSM}	non-repetitive peak reverse current	t _p = 100 μs	_	0.5	Α
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	125	°C
T _{amb}	operating ambient temperature		-65	+125	°C

ELECTRICAL CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
Per diode					
V _F	forward voltage	see Fig.3			
		I _F = 100 mA	260	300	mV
		I _F = 1 A	400	450	mV
I _R	reverse current	V _R = 20 V; note 1; see Fig.4	80	500	μА
		$V_R = 25 \text{ V}$; note 1; see Fig.4	_	1	mA
		$V_R = 20 \text{ V}; T_j = 100 ^{\circ}\text{C}; \text{ note } 1$	_	10	mA
C _d	diode capacitance	$f = 1 \text{ MHz}$; $V_R = 4 \text{ V}$; see Fig.5	100	_	pF

Note

1. Pulse test: t_p = 300 μ s; δ = 0.02.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	100	K/W

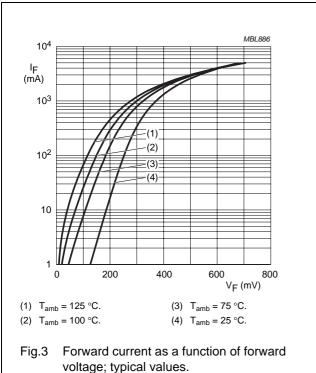
Note

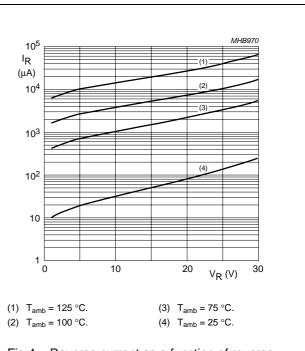
1. Refer to SOT223 standard mounting conditions.

Schottky barrier double diodes

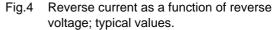
BAT120 series

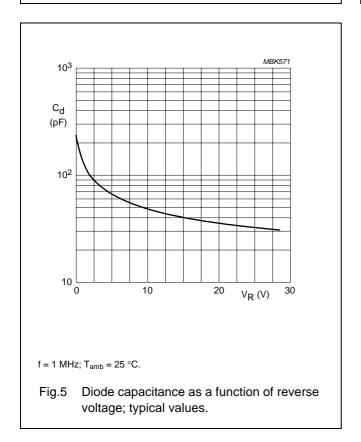
GRAPHICAL DATA





voltage; typical values.





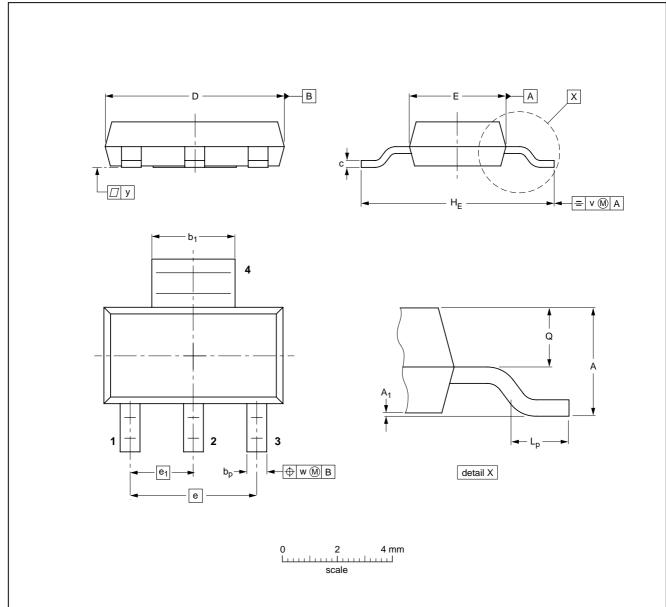
Schottky barrier double diodes

BAT120 series

PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 4 leads

SOT223



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	bp	b ₁	С	D	E	е	e ₁	HE	Lp	Q	v	w	у
mm	1.8 1.5	0.10 0.01	0.80 0.60	3.1 2.9	0.32 0.22	6.7 6.3	3.7 3.3	4.6	2.3	7.3 6.7	1.1 0.7	0.95 0.85	0.2	0.1	0.1

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT223			SC-73			97-02-28 99-09-13

Schottky barrier double diodes

BAT120 series

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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- 2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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